

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU012** is Designed for TV Band IV & V Applications.

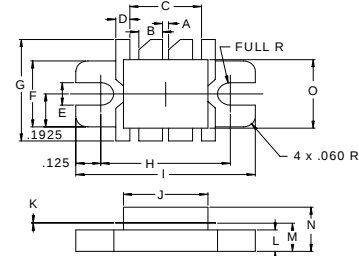
FEATURES:

- Input Matching Network
- Common emitter
- **Omnigold™** Metalization System with eutectic die bonding

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.6 $^\circ\text{C/W}$

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.030 / 0.76
B	.115 / 2.92	.125 / 3.18
C		.360 / 9.14
D	.065 / 1.65	.075 / 1.91
E		.130 / 3.30
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

ORDER CODE: ASI10646

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50\text{ mA}$	35			V
BV_{CER}	$I_C = 50\text{ mA}$ $R_{BE} = 10\ \Omega$	60			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_E = 28\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		100	---
P_G IMD_1	$V_{CE} = 26.5\text{ V}$ $I_C = 2 \times 0.85\text{ mA}$ $f = 860\text{ MHz}$ $P_{OUT} = 12\text{ W}$	9.0 -52			dB dBc